

CMBT3904E NPN
CMBT3906E PNP

**ENHANCED SPECIFICATION
SURFACE MOUNT
COMPLEMENTARY
SILICON TRANSISTORS**

FEMTOmini™



SOT-923 CASE



www.centra-semi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMBT3904E (NPN) and CMBT3906E (PNP) are general purpose transistors with enhanced specifications. These devices are ideal for applications where ultra small size and power dissipation are the prime requirements. Packaged in the **FEMTOmini™** SOT-923 package, these transistors provide performance characteristics suitable for the most demanding size constrained applications.

**MARKING CODES: CMBT3904E: B
CMBT3906E: G**

FEATURES

- Very Small Package Size
- 200mA Collector Current
- Low $V_{CE(SAT)}$ (0.1V Typ @ 50mA)
- Miniature 0.8 x 0.6 x 0.4mm
Ultra Low height profile
FEMTOmini™ Surface Mount Package

APPLICATIONS

- DC / DC Converters
- Voltage Clamping
- Protection Circuits
- Battery powered applications including:
Cell Phones, Digital Cameras, Pagers,
PDAs, Laptop Computers, etc.

MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$)

◆ Collector-Base Voltage
Collector-Emitter Voltage
◆ Emitter-Base Voltage
Continuous Collector Current
Power Dissipation
Operating and Storage Junction Temperature
Thermal Resistance

SYMBOL		UNITS
V_{CBO}	60	V
V_{CEO}	40	V
V_{EBO}	6.0	V
I_C	200	mA
P_D	100	mW
T_J, T_{stg}	-65 to +150	$^\circ\text{C}$
θ_{JA}	1250	$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS: ($T_A=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	NPN TYP	PNP TYP	MAX	UNITS
I_{CEV}	$V_{CE}=30\text{V}, V_{EB}=3.0\text{V}$				50	nA
◆ BV_{CBO}	$I_C=10\mu\text{A}$	60	115	90		V
BV_{CEO}	$I_C=1.0\text{mA}$	40	60	55		V
◆ BV_{EBO}	$I_E=10\mu\text{A}$	6.0	7.5	7.9		V
◆ $V_{CE(SAT)}$	$I_C=10\text{mA}, I_B=1.0\text{mA}$		0.057	0.050	0.100	V
◆ $V_{CE(SAT)}$	$I_C=50\text{mA}, I_B=5.0\text{mA}$		0.100	0.100	0.200	V
$V_{BE(SAT)}$	$I_C=10\text{mA}, I_B=1.0\text{mA}$	0.650	0.750	0.750	0.850	V
$V_{BE(SAT)}$	$I_C=50\text{mA}, I_B=5.0\text{mA}$		0.850	0.850	0.950	V

- ◆ Enhanced specification.

R1 (8-January 2010)

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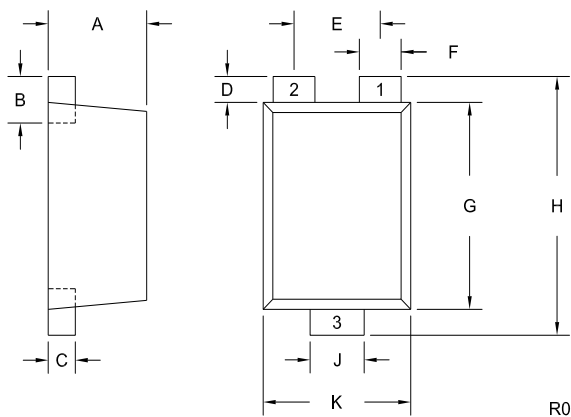


ELECTRICAL CHARACTERISTICS - Continued:
SYMBOL TEST CONDITIONS

		MIN	TYP	NPN TYP	PNP MAX	UNITS
♦ h_{FE}	$V_{CE}=1.0V, I_C=0.1mA$	90	240	130		
♦ h_{FE}	$V_{CE}=1.0V, I_C=1.0mA$	100	235	150		
h_{FE}	$V_{CE}=1.0V, I_C=10mA$	100	215	150	300	
♦ h_{FE}	$V_{CE}=1.0V, I_C=50mA$	70	110	120		
h_{FE}	$V_{CE}=1.0V, I_C=100mA$	30	50	55		
f_T	$V_{CE}=20V, I_C=10mA, f=100MHz$	300				MHz
C_{ob}	$V_{CB}=5.0V, I_E=0, f=1.0MHz$				4.0	pF
C_{ib}	$V_{BE}=0.5V, I_C=0, f=1.0MHz$				8.0	pF
h_{ie}	$V_{CE}=10V, I_C=1.0mA, f=1.0kHz$	1.0			12	k Ω
h_{re}	$V_{CE}=10V, I_C=1.0mA, f=1.0kHz$	0.1			10	$\times 10^{-4}$
h_{fe}	$V_{CE}=10V, I_C=1.0mA, f=1.0kHz$	100			400	
h_{oe}	$V_{CE}=10V, I_C=1.0mA, f=1.0kHz$	1.0			60	μS
NF	$V_{CE}=5.0V, I_C=100\mu A, R_S=1.0k\Omega,$ $f=10Hz$ to $15.7kHz$				4.0	dB
t_d	$V_{CC}=3.0V, V_{BE}=0.5V, I_C=10mA, I_{B1}=1.0mA$				35	ns
t_r	$V_{CC}=3.0V, V_{BE}=0.5V, I_C=10mA, I_{B1}=1.0mA$				35	ns
t_s	$V_{CC}=3.0V, I_C=10mA, I_{B1}=I_{B2}=1.0mA$				200	ns
t_f	$V_{CC}=3.0V, I_C=10mA, I_{B1}=I_{B2}=1.0mA$				50	ns

♦ Enhanced specification.

SOT-923 CASE - MECHANICAL OUTLINE



DIMENSIONS				
SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.015	0.016	0.39	0.41
B	0.004	0.010	0.10	0.26
C	0.003	0.006	0.08	0.14
D	0.002	0.006	0.05	0.15
E	0.014		0.35	
F	0.005	0.009	0.12	0.22
G	0.030	0.033	0.75	0.85
H	0.035	0.043	0.90	1.10
J	0.007	0.011	0.17	0.27
K	0.022	0.026	0.55	0.65

SOT-923 (REV: R0)

LEAD CODE:

- 1) BASE
- 2) EMITTER
- 3) COLLECTOR

MARKING CODES:

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OUTSTANDING SUPPORT AND SUPERIOR SERVICES



PRODUCT SUPPORT

Central's operations team provides the highest level of support to insure product is delivered on-time.

- Supply management (Customer portals)
- Inventory bonding
- Consolidated shipping options
- Custom bar coding for shipments
- Custom product packing

DESIGNER SUPPORT/SERVICES

Central's applications engineering team is ready to discuss your design challenges. Just ask.

- Free quick ship samples (2nd day air)
- Online technical data and parametric search
- SPICE models
- Custom electrical curves
- Environmental regulation compliance
- Customer specific screening
- Up-screening capabilities
- Special wafer diffusions
- PbSn plating options
- Package details
- Application notes
- Application and design sample kits
- Custom product and package development

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